NCE N-Channel Super Trench Power MOSFET

Description

The series of devices uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{\text{DS(ON)}}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

Application

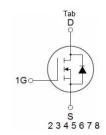
- DC/DC Converter
- •Ideal for high-frequency switching and synchronous rectification

General Features

- V_{DS} =200V, I_D =100A $R_{DS(ON)}$ =9.0m Ω , typical@ V_{GS} =10V
- Excellent gate charge x R_{DS(on)} product(FOM)
- Very low on-resistance R_{DS(on)}
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS Tested
- 100% △ Vds Tested

TOLL-8L





Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP02T10LL	NCEP02T10LL	TOLL-8L	Ø330mm	24mm	2000 units

Absolute Maximum Ratings (T_c=25℃unless otherwise noted)

		,			
Parameter	Symbol	Limit	Unit		
Drain-Source Voltage	V _{DS}	200	V		
Gate-Source Voltage	V _G s	±20	V		
Drain Current-Continuous	I _D	100	А		
Drain Current-Continuous(T _C =100 °C)	I _D (100℃)	80	А		
Pulsed Drain Current	I _{DM}	400	А		
Maximum Power Dissipation	P _D	400	W		
Derating factor		2.67	W/℃		
Single pulse avalanche energy (Note 1)	E _{AS}	1216	mJ		
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55 To 175	$^{\circ}$ C		

Thermal Characteristic

Thermal Resistance,Junction-to-Case	Rejc	0.38	°C/W

NCEP02T10LL

Electrical Characteristics (T_C=25 ℃ unless otherwise noted)

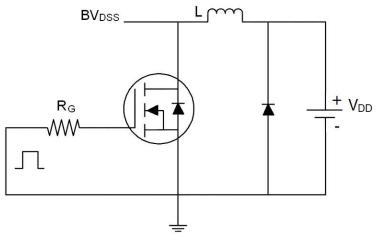
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	200	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =200V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics						
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS},I_{D}=250\mu A$	2.0	3.0	4.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =20A	-	9.0	11.5	mΩ
Forward Transconductance	g FS	V _{DS} =10V,I _D =50A	70	-	-	S
Dynamic Characteristics						
Input Capacitance	C _{lss}	\/ 400\/\/ 0\/	-	6000	-	PF
Output Capacitance	Coss	V _{DS} =100V,V _{GS} =0V,	-	425	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.0MHz	-	16	-	PF
Switching Characteristics (Note 2)						
Turn-on Delay Time	t _{d(on)}		-	18	-	nS
Turn-on Rise Time	t _r	V_{DD} =100 V , I_{D} =50 A	-	26	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10 V , R_{G} =4.7 Ω	-	41	-	nS
Turn-Off Fall Time	t _f		-	11	-	nS
Total Gate Charge	Qg	\/ 400\/ L 50A	-	87		nC
Gate-Source Charge	Q _{gs}	V _{DS} =100V,I _D =50A,	-	32		nC
Gate-Drain Charge	Q _{gd}	V _{GS} =10V	-	17.5		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage	V _{SD}	V _{GS} =0V,I _S =100A	-		1.2	V
Diode Forward Current	Is		-	-	100	Α
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = 50A	-	140		nS
Reverse Recovery Charge	Qrr	di/dt = 100A/μs	-	600		nC

Notes:

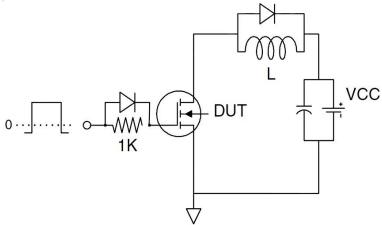
- 1. EAS condition : Tj=25 $^{\circ}\text{C}$,VDD=50V,VG=10V,L=0.5mH,Rg=25 Ω
- 2. Guaranteed by design, not subject to production
- 3. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=175°C. The SOA curve provides a single pulse rating.

Test Circuit

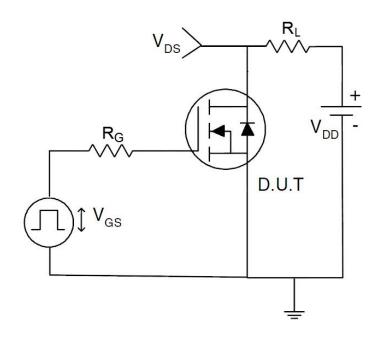
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics

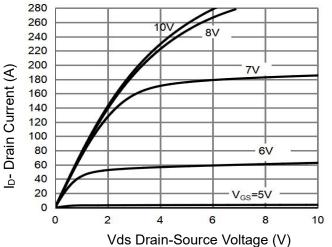


Figure 1 Output Characteristics

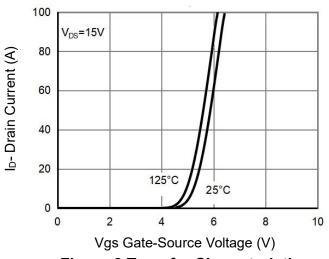


Figure 2 Transfer Characteristics

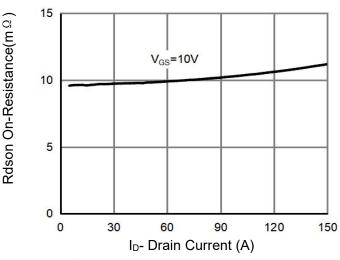


Figure 3 Rdson- Drain Current

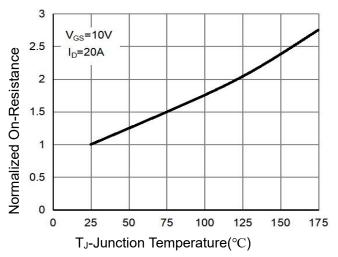


Figure 4 Rdson-JunctionTemperature

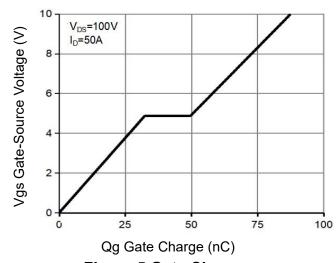


Figure 5 Gate Charge

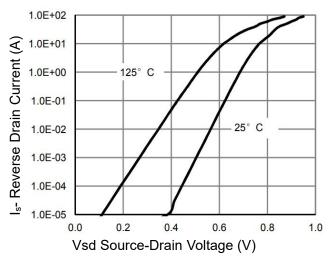


Figure 6 Source- Drain Diode Forward

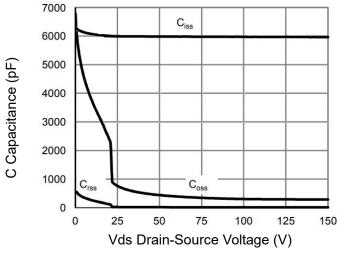


Figure 7 Capacitance vs Vds

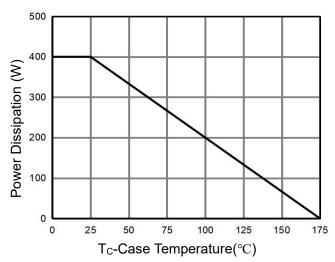


Figure 9 Power De-rating

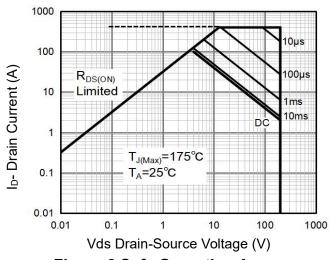


Figure 8 Safe Operation Area (Note3)

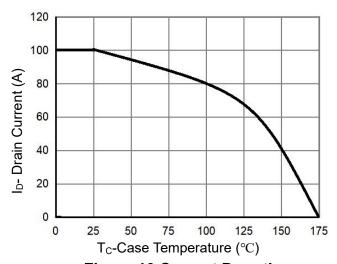


Figure 10 Current De-rati

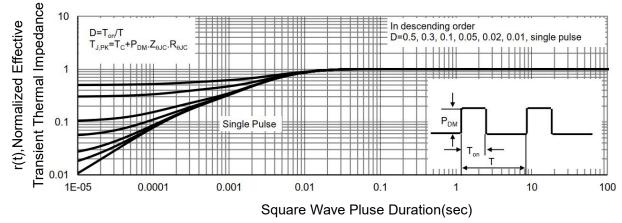
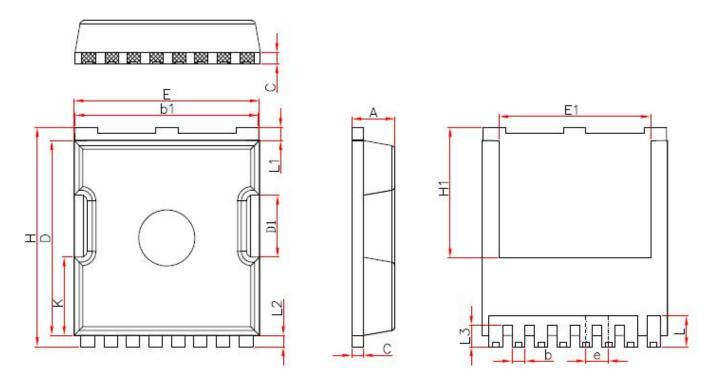


Figure 11 Normalized Maximum Transient Thermal Impedance

TOLL-8L Package Information



Symbol	Millimeters			
1000	Min.	Nom.	Max.	
A	2.20	2.30	2.40	
b	0.65	0.75	0.85	
b1	9.70	9.80	9.90	
С	0.50	0.60	0.70	
D	10.30	10.40	10.50	
D1	3.15	3.3	3.45	
Е	9.70	9.90	10.10	
E1	8.00	8.10	8.20	
е	1.10	1.20	1.30	
Н	11.6	11.7	11.8	
H1	6.85	6.95	7.05	
K	4.08	4.18	4.28	
L	1.60	1.65	2.10	
L1	0.60	0.70	0.80	
L2	0.50	0.60	0.70	
L3	1.05	1.20	1.30	

NCEP02T10LL

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